NSN 5961-01-332-8089

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-332-8089 **Inclosure Material:** Plastic **Overall Length:** Between 0.072 inches and 0.078 inches **Overall Height:** Between 0.030 inches and 0.040 inches Overall Width: Between 0.037 inches and 0.043 inches **Function For Which Designed:** Zener diode **Mounting Method: Terminal Features Provided:** Gold plated leads **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 6.46 breakdown voltage, dc and 7.14 breakdown voltage, dc **Current Rating Per Characteristic:** 50.00 microamperes reverse current, dc **Power Rating Per Characteristic:** 360.0 milliwatts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Precious Material And Location:** Eutetic die bonds, surface terminals -land areas- a gold **Precious Material:** Gold **Test Data Document:** 98897-mil-s-19500/127 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 4 bonding pad Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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